

ABSTRACT

On the occasion of the aligning process to transfer a predetermined pattern to a semiconductor wafer by irradiating a photoresist on the semiconductor wafer with an aligning laser beam of the modified lighting via a photomask MK, the photomask MK allocating, to provide periodicity, the main apertures to transfer the predetermined pattern as the apertures formed by removing a part of the half-tone film on the mask substrate and the auxiliary apertures not resolved on the semiconductor wafer as the apertures formed by removing a part of the half-tone film is used to improve the resolution of the pattern.